

BGT24LTR11N16

Silicon Germanium 24GHz Radar
Transceiver MMIC

Data Sheet

Revision: 1.2

RF and Protection Devices

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Data Sheet

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| Page | Subjects (major changes since last revision) |
|-------------|---|
| 7 | Attention note is added |
| 9 | Divider specification is changed |
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1 Introduction



1.1 Features

- 24GHz transceiver MMIC
- Fully integrated low phase noise VCO
- Built in temperature compensation circuit for VCO stabilization
- Homodyne quadrature receiver
- Frequency divider
- Low power consumption
- Fully ESD protected device
- Single ended RF and IF terminals
- 200 GHz bipolar SiGe:C technology b7hf200
- Single supply voltage 3.3V
- TSNP-16-9 plastic package
- Pb-free (RoHS compliant) package

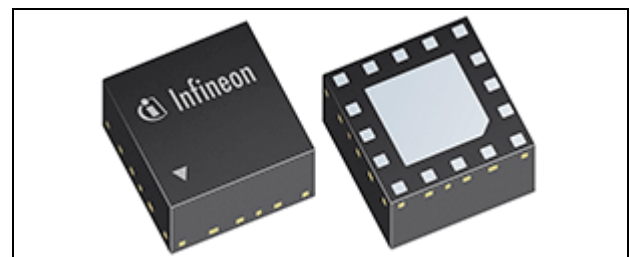


Figure 1 BGT24LTR11N16 in TSNP-16-9

Description

The BGT24LTR11 is a Silicon Germanium Transceiver MMIC operating from 24.0 GHz up to 24.25 GHz. It is based on a 24 GHz fundamental voltage controlled oscillator (VCO). A built in voltage source delivers a VCO tuning voltage (V_{PTAT}) which is proportional to absolute temperature. When connected to the VCO tuning pin (V_{TUNE}) it compensates for the inherent frequency drift of the VCO over temperature thus stabilizing the VCO within the ISM band eliminating the need for a PLL/Microcontroller. An integrated 1:16 frequency divider also allows for external phase lock loop VCO frequency stabilization.

The receiver section uses a low noise amplifier (LNA) in front of a quadrature homodyne down conversion mixer in order to provide excellent receiver sensitivity. Derived from the internal VCO signal, a RC polyphase filter (PPF) generates quadrature LO signals for the quadrature mixer. The I/Q IF outputs are available through a single ended terminal respectively.

The device is manufactured in a 0.18 μ m SiGe:C technology offering a cutoff frequency of 200 GHz. It is packaged in a 16 pin leadless RoHS compliant TSNP package.

| Product Name | Package | Chip | Marking |
|---------------|-----------|-------|---------|
| BGT24LTR11N16 | TSNP-16-9 | T1811 | LTR11 |

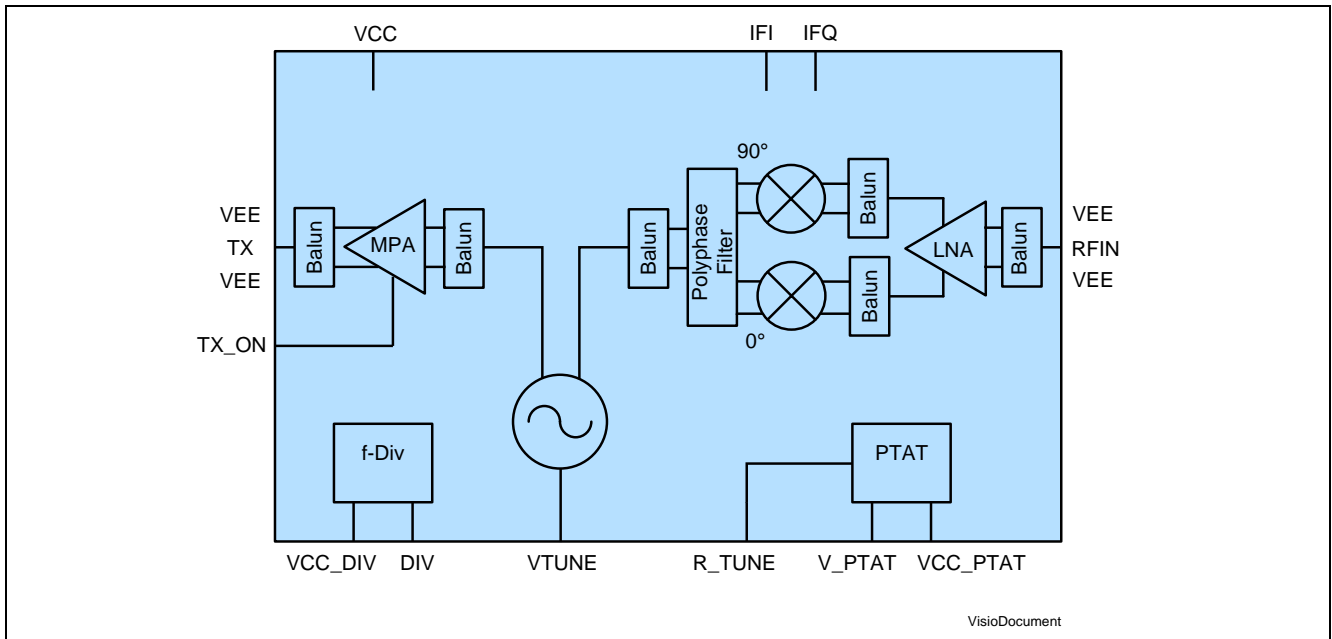


Figure 2 BGT24LTR11N16 block diagram

2 Electrical Characteristics

2.1 Absolute Maximum Ratings

Table 1 Absolute maximum ratings: $T_A = -40\text{ °C} \dots 85\text{ °C}$; all voltages with respect to ground

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|-------------------------------------|----------------|-------|------|----------------|------|---|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | -0.3 | | 3.6 | V | |
| Supply voltage divider | V_{CC_DIV} | -0.3 | | 3.6 | V | |
| Supply voltage PTAT voltage source | V_{CC_PTAT} | -0.3 | | 3.6 | V | |
| DC voltage at RF pins | V_{DC_RF} | | | 0 | | MMIC provides short circuit to GND for RF_IN and TX_OUT |
| Voltage applied to none-RF I/O pins | $V_{DC_I/O}$ | -0.3 | | $V_{CC} + 0.3$ | V | |
| Total power dissipation | P | | | 300 | mW | |
| Ambient temperature range | T_A | -40 | | 85 | °C | |
| Storage temperature range | T_{STG} | -50 | | 125 | °C | |

Attention: Stresses exceeding the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the integrated circuit.

2.2 ESD Integrity

Table 2 ESD integrity

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---------------------------------|---------------|-------|------|------|------|-------------------------|
| | | Min. | Typ. | Max. | | |
| ESD robustness HBM ¹ | $V_{ESD-HBM}$ | -1 | | 1 | kV | |
| ESD robustness CDM ² | $V_{ESD-CDM}$ | -500 | | 500 | V | |

1) According to ANSI/ESDA/JEDEC JS-001 (R = 1.5kOhm, C = 100pF) for Electrostatic Discharge Sensitivity Testing, Human Body Model (HBM)-Component Level

2) According to JEDEC JESD22-C101 Field-Induced Charged Device Model (CDM), Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components

Please note that this result is subject to:

- lot variations within the manufacturing process as specified by Infineon
- changes in the specific test setup

2.3 Power Supply

Table 3 Power supply characteristics: $T_A = -40\text{ °C} \dots 85\text{ °C}$

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|----------------|----------|-------|------|------|------|-------------------------|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC} | 3.2 | 3.3 | 3.4 | V | |

Table 3 Power supply characteristics: $T_A = -40\text{ }^{\circ}\text{C} \dots 85\text{ }^{\circ}\text{C}$

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|----------------|----------|----------|------|------|---------------|-------------------------|
| | | Min. | Typ. | Max. | | |
| Supply current | I_{CC} | | 45 | 55 | mA | |
| Duty cycle | | 1 : 1000 | | 1 | | |
| Pulse duration | t_P | 1 | | | μs | |

2.4 TX Section

Table 4 TX characteristics: $T_A = -40\text{ }^{\circ}\text{C} \dots 85\text{ }^{\circ}\text{C}$

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---|---------------------|--------|------|------------|---------------|---|
| | | Min. | Typ. | Max. | | |
| VCO frequency range | f_{VCO} | 24.050 | | 24.250 | GHz | V_PTAT connected to VTUNE; 16 kOhm resistor connected from R_TUNE to GND |
| VCO phase noise | P_N | | | -55 -80 | dBc/ Hz | @ 10 kHz offset @ 100 kHz offset |
| VCO AM noise | P_{AM} | | | -135 | dBc/ Hz | @ 100 kHz offset |
| Tuning voltage to cover VCO frequency range | $VTUNE$ | 0.7 | | 2.5 | V | |
| VCO tuning sensitivity within VCO frequency range | | | 720 | 2000 | MHz/V | |
| Harmonic suppression | | 25 | | | dBc | |
| Non-harmonic suppression | | 62 | | | dBc | $f > 10\text{ GHz}$; $D_{DIV}=16$ |
| Non-harmonic suppression | | 45 | | | dBc | $f \leq 10\text{ GHz}$; $D_{DIV}=16$ |
| TX output power | P_{TX} | 2 | 6 | 10 | dBm | |
| TX load impedance | Z_{TXOUT} | | 50 | | Ω | Single ended |
| TX_ON low level input voltage | $V_{TX_ON_low}$ | | | 0.8 | V | |
| TX_ON high level input voltage | $V_{TX_ON_high}$ | 2 | | | V | |
| TX_ON input voltage hysteresis | $V_{TX_ON_hys}$ | 50 | | | mV | |
| TX_ON input current | I_{TX_ON} | -100 | | 100 | μA | |
| TX_ON switching time | t_{TX_ON} | | | 2 | ns | |
| Power up TX settling time | $t_{TX_Power_up}$ | | | 100ns | | Defines the time TX section requires to settle after VCC supply voltage is within specified range |

2.5 RX Section (Measured with TX_ON=0V)

Table 5 RX characteristics: T_A = -40 °C ... 85 °C

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|------------------------------|--------------|-------|------|-------|------------|---|
| | | Min. | Typ. | Max. | | |
| RX frequency range | f_{RX} | 24.0 | | 24.25 | GHz | |
| RX input impedance | Z_{RXIN} | | 50 | | Ω | Single ended |
| Voltage conversion gain | G_C | 15.5 | 20 | 26.5 | dB | |
| SSB noise figure | NF_{SSB} | | 10 | 18 | dB | Single sideband @ $f_{IF} = 100$ kHz |
| Input compression point | IP_{1dB} | -28 | | | dBm | |
| Quadrat. phase imbalance | ϵ_P | 0 | | 24 | deg | |
| Quadrat. amplitude imbalance | ϵ_A | -1 | | 1 | dB | |
| IF output impedance | Z_{IF} | | | 1 | k Ω | Single ended |

2.6 Frequency Divider

Table 6 Frequency divider characteristics: T_A = -40 °C ... 85 °C

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|---|----------------|-------|------|------|------|--|
| | | Min. | Typ. | Max. | | |
| Prescaler division ratio | D_{DIV} | 16 | | 8192 | - | 16 if $V_{CC_PTAT} = 0$ V, 8192 if $V_{CC_PTAT} = 3.3$ V |
| Prescaler output voltage for division ratio 16 | V_{DIV16} | 60 | 120 | 350 | mV | Peak to Peak voltage when DIV_OUT is terminated with 50 Ohm and $D_{DIV}=16$ |
| Prescaler output "high" voltage for division ratio 8192 | $V_{DIV8192H}$ | 2.4 | | | V | DIV_OUT is loaded with 1M Ω m, 13 pF |
| Prescaler output "low" voltage for division ratio 8192 | $V_{DIV8192L}$ | | | 0.8 | V | DIV_OUT is loaded with 1M Ω m, 13 pF |
| Prescaler supply voltage | V_{CC_DIV} | 3.2 | 3.3 | 3.4 | V | |
| Prescaler supply current | I_{CC_DIV} | 13 | 19 | 25 | mA | |

2.7 Proportional to absolute temperature (PTAT) voltage source

Table 7 PTAT voltage source characteristics: T_A = -40 °C ... 85 °C

| Parameter | Symbol | Value | | | Unit | Note/ Test Condition |
|----------------|-----------------|-------|------|------|------|-------------------------|
| | | Min. | Typ. | Max. | | |
| Supply voltage | V_{CC_PTAT} | 3.2 | 3.3 | 3.4 | V | |
| Supply current | I_{CC_PTAT} | | 1.5 | 2.5 | mA | |
| Output voltage | V_{OUT_PTAT} | 0.7 | 1.3 | 2 | V | |

3 Pin description

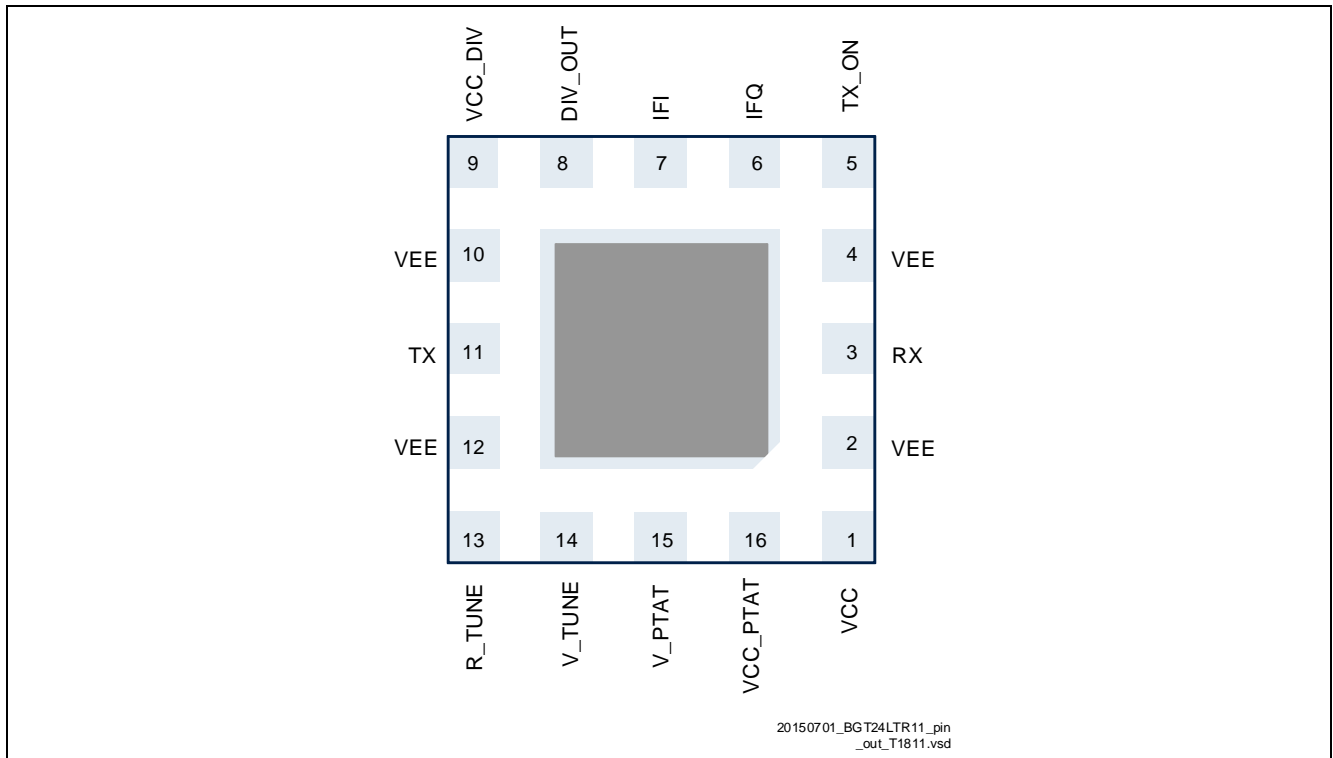
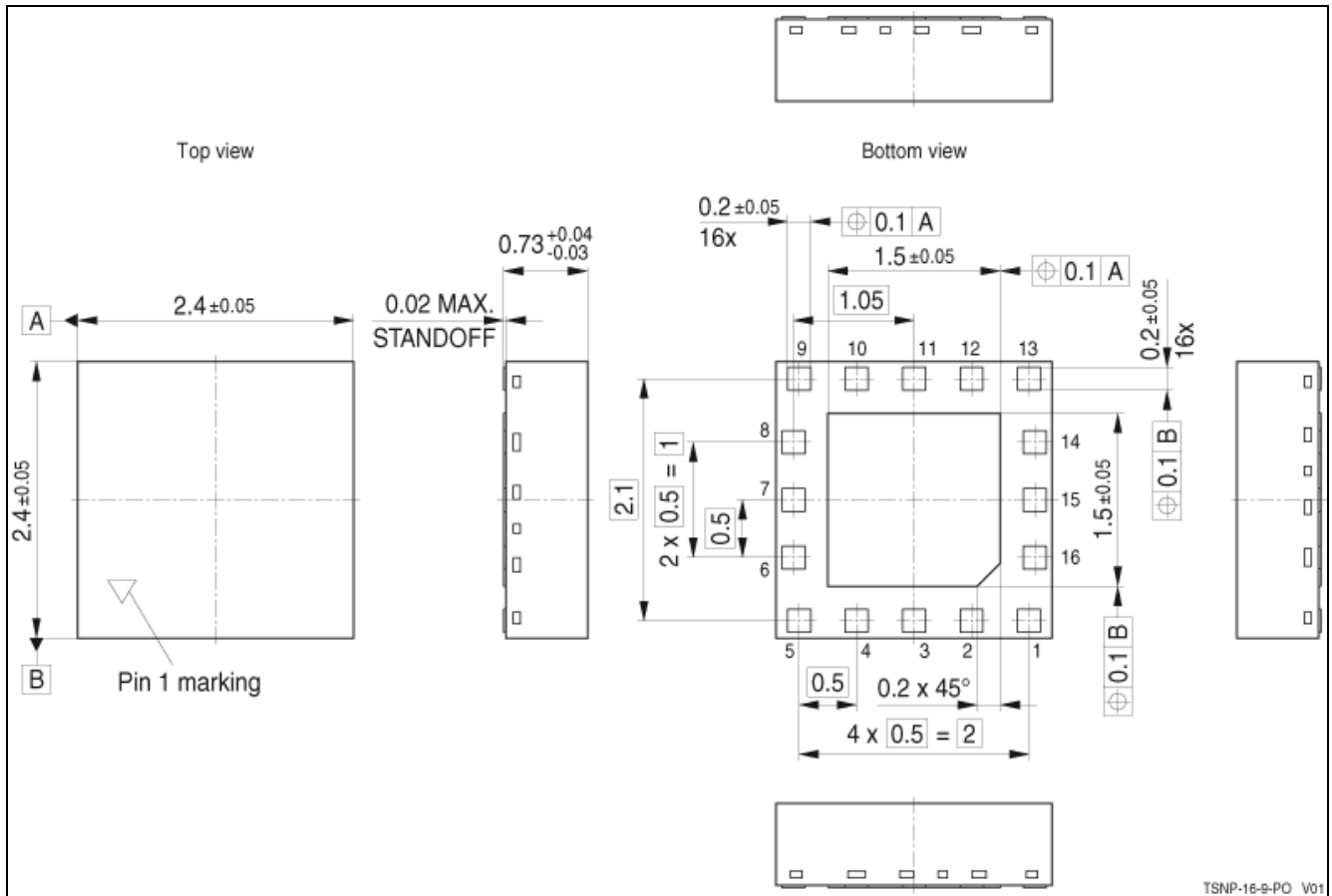


Figure 3 Pin-out (top view)

Table 8 Pin definition and function

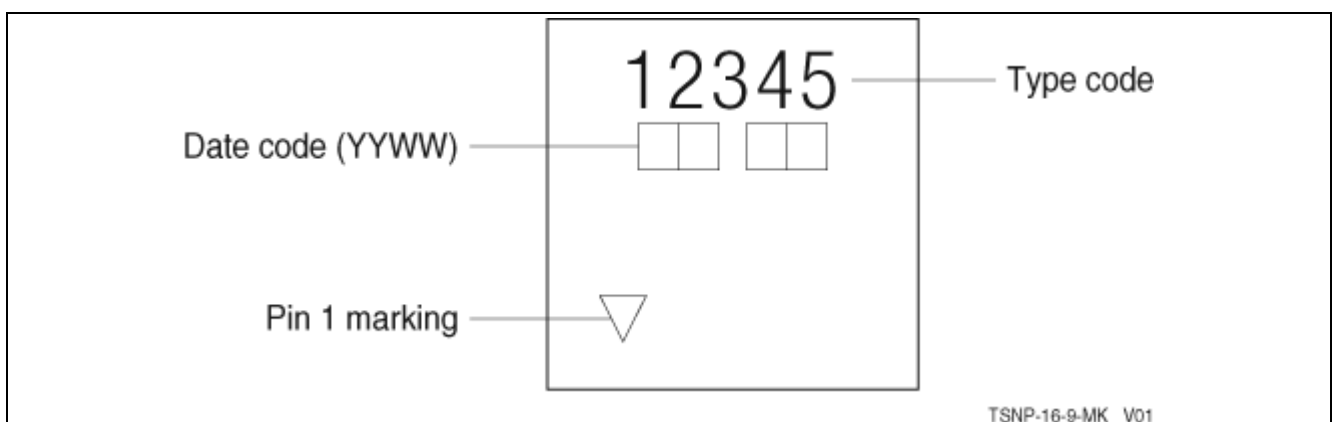
| Pin Number | Name | Function |
|------------|----------|---|
| 1 | VCC | Supply voltage |
| 2 | VEE | Ground |
| 3 | RX | Receiver RF input |
| 4 | VEE | GND |
| 5 | TX_EN | Output power enable |
| 6 | IFQ | Quadrature phase down converter IF output |
| 7 | IFI | In phase down converter IF output |
| 8 | DIV_OUT | Frequency divider output |
| 9 | VCC_DIV | Supply voltage of prescaler |
| 10 | VEE | Ground |
| 11 | TX | Tranmitter RF output |
| 12 | VEE | Ground |
| 13 | R_TUNE | VCO operating frequency band select |
| 14 | V_TUNE | VCO frequency tuning input |
| 15 | V_PTAT | PTAT voltage source output |
| 16 | VCC_PTAT | PTAT voltage source power supply |

4 Physical Dimension



TSNP-16-9-PO V01

Figure 4 Package Outline (top, side and bottom view) of TSNP-16-9



TSNP-16-9-MK V01

Figure 5 Marking Layout of TSNP-16-9 (example)

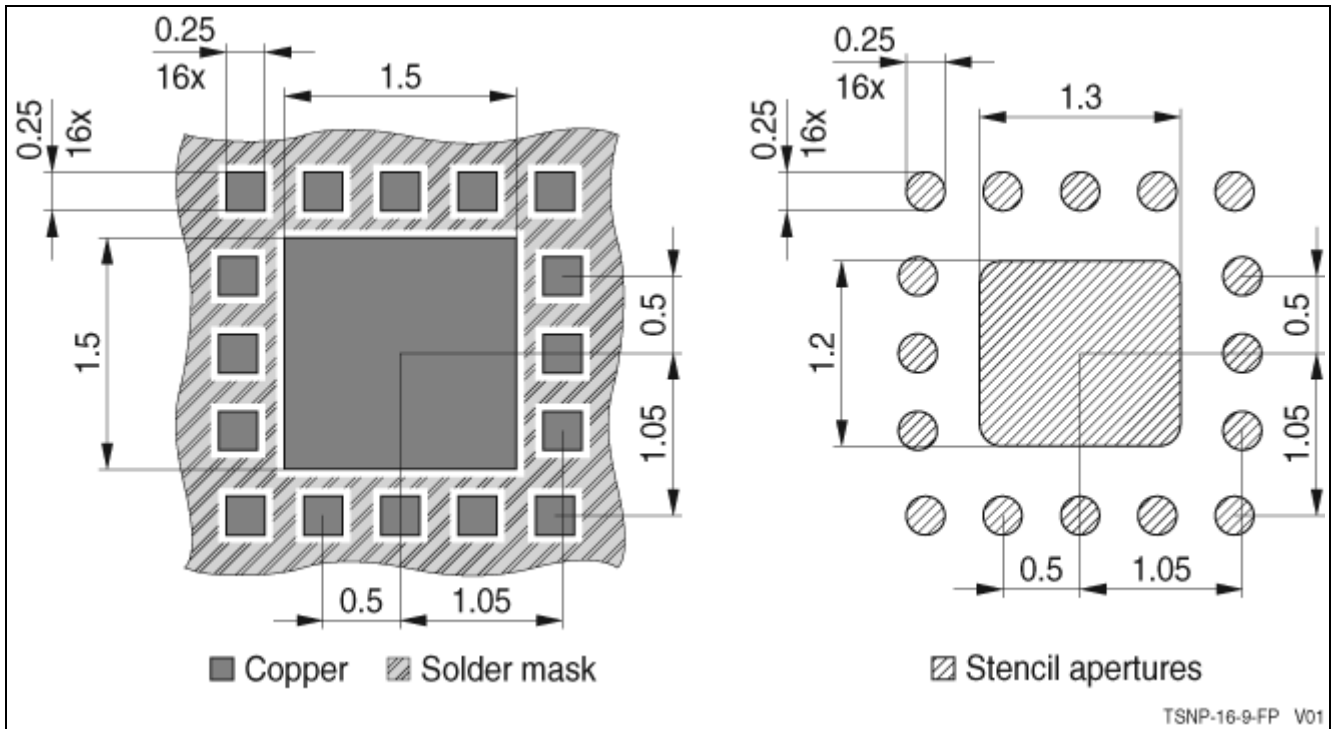


Figure 6 Soldering Footprint of TSNP-16-9

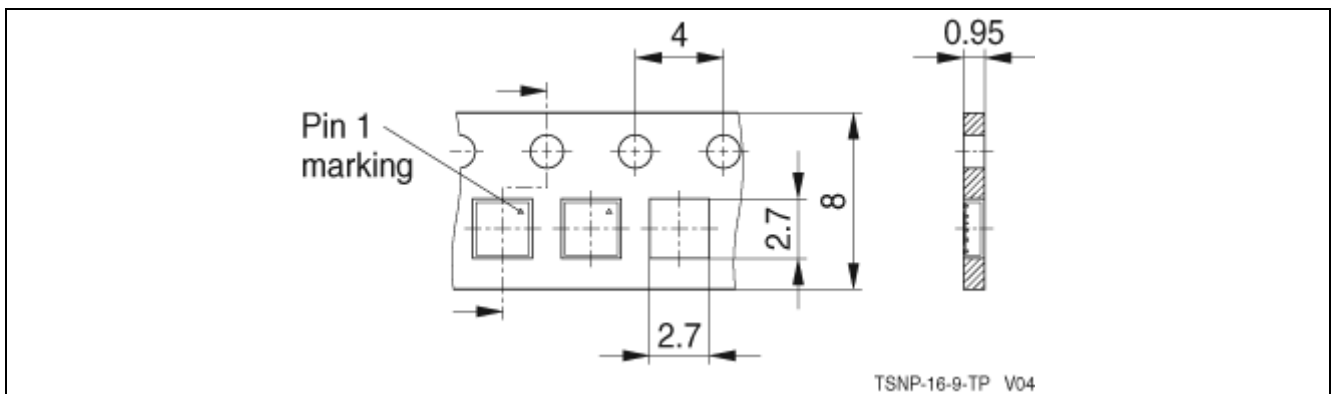


Figure 7 Packing Description of TSNP-16-9; Ø Reel: 180 mm, Pieces / Reel: 3000, Reels / Box: 1

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